

DARTWARS

Detector Array Readout with Traveling Wave Amplifiers

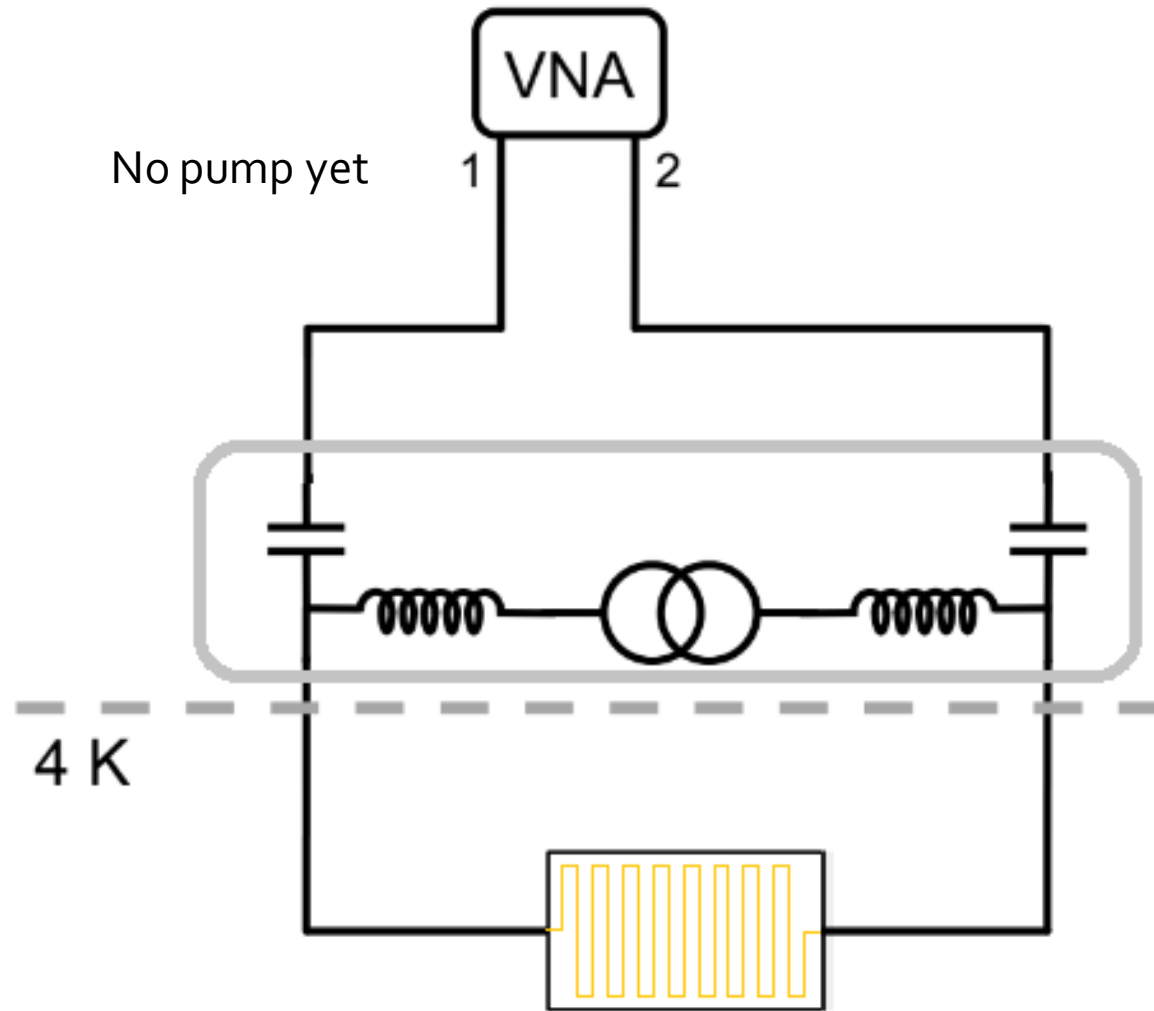
Update report on experimental activity in Milano-Bicocca

by Andrea Celotto

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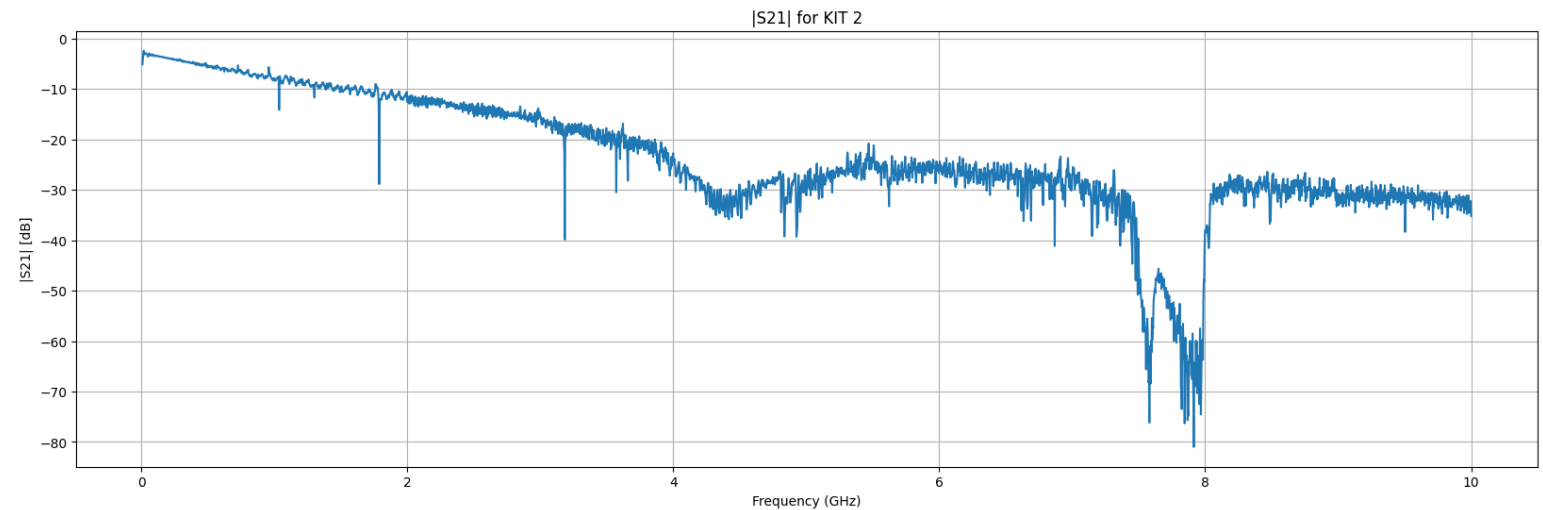
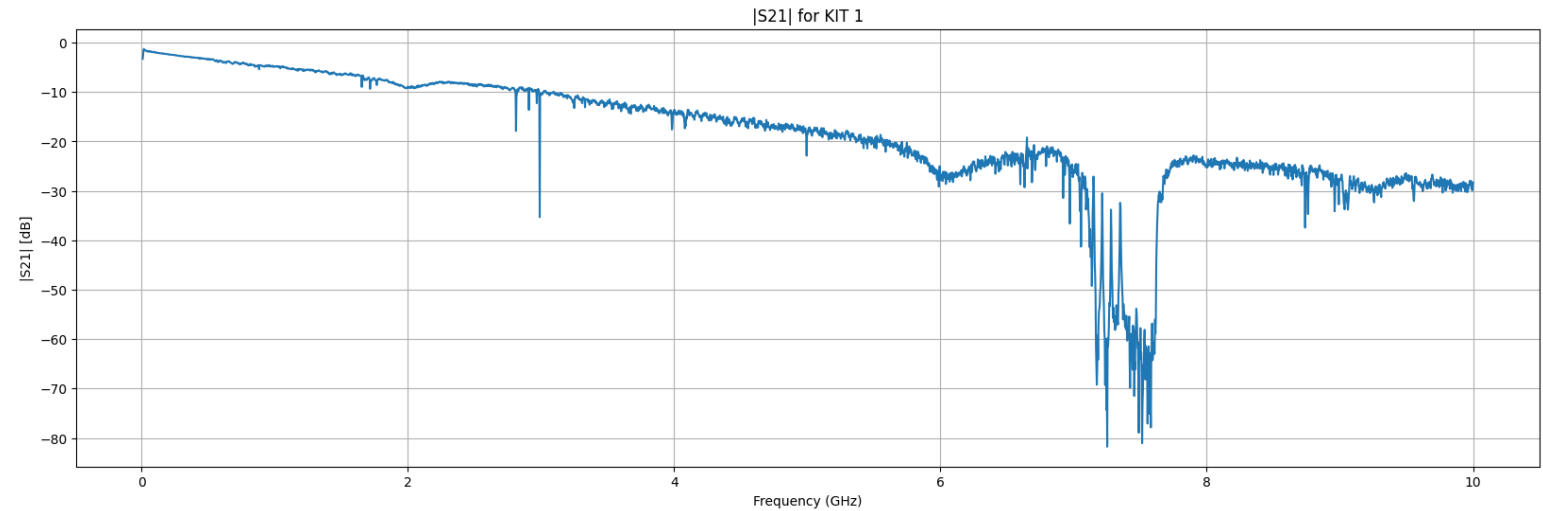
Experimental setup

- I can place two devices at 4 K



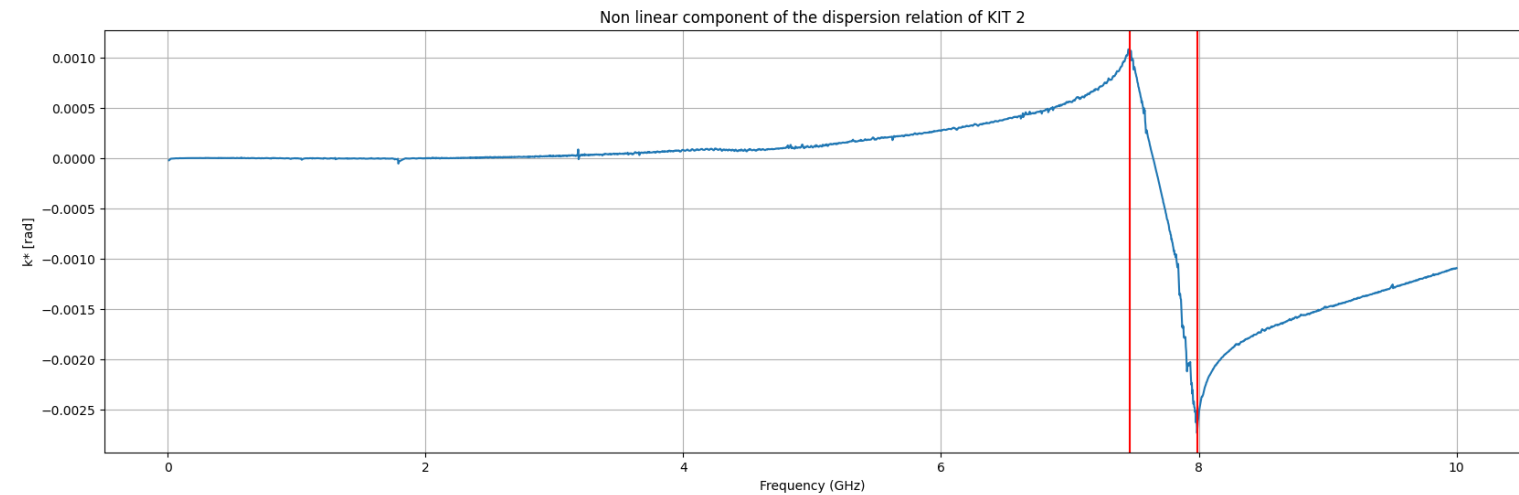
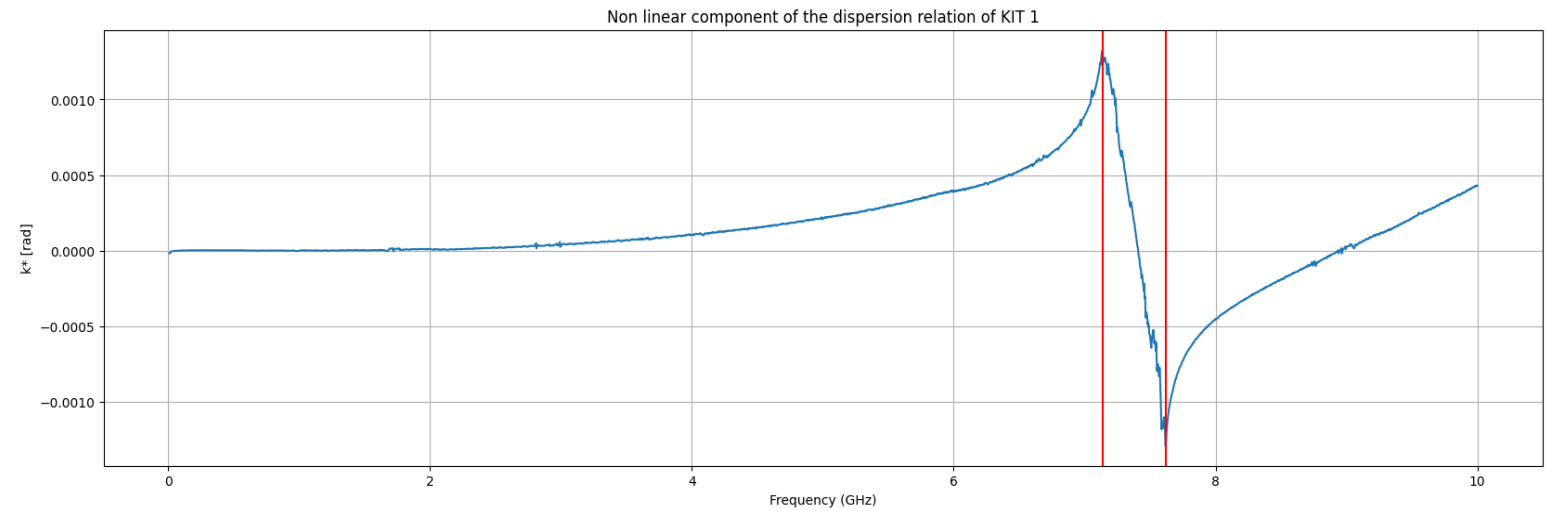
First look at $|S_{21}|$ traces

- Measurements w/o the bias tee.
- The bandgap is showing



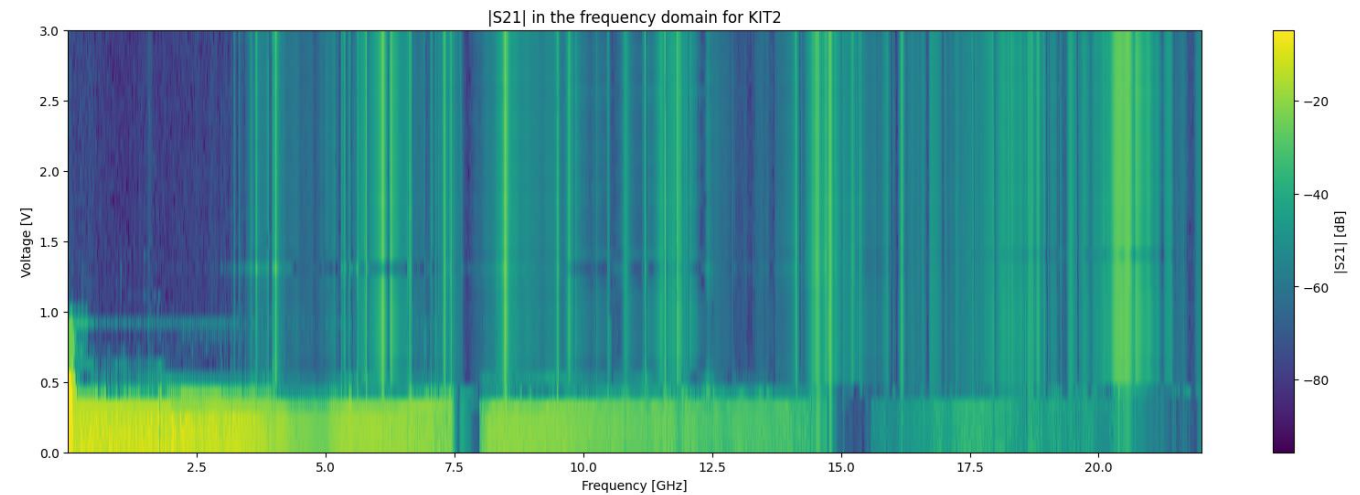
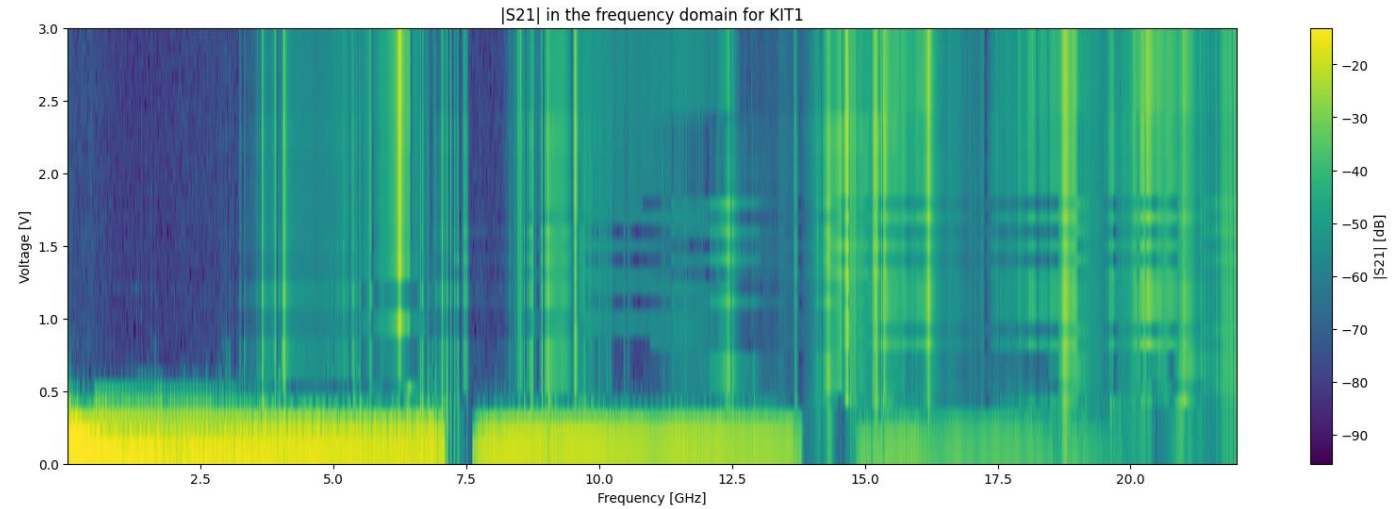
First look at $\arg(S_{21})$

- If I isolate the non-linear component I can assess the stopband location
- KIT 1: (7.137 - 7.618) GHz
- KIT 2: (7.462 - 7.983) GHz



Biasing breaks superconductivity

- At small bias the stopband is clearly visible
- Increasing the bias over 0.7 mA superconductivity seems to break.
- Regardless of the reasons, a transition is evident

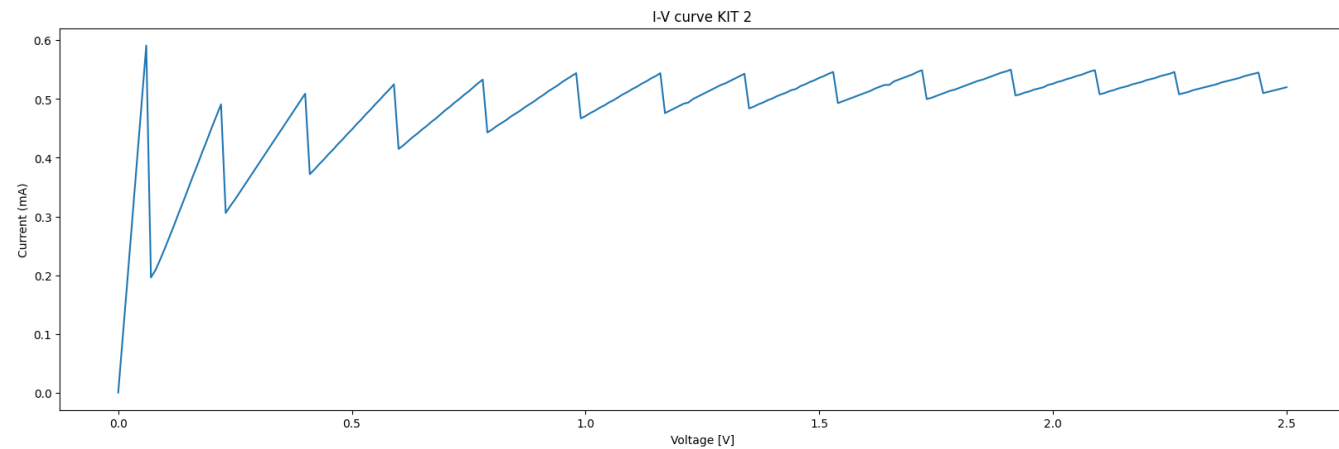
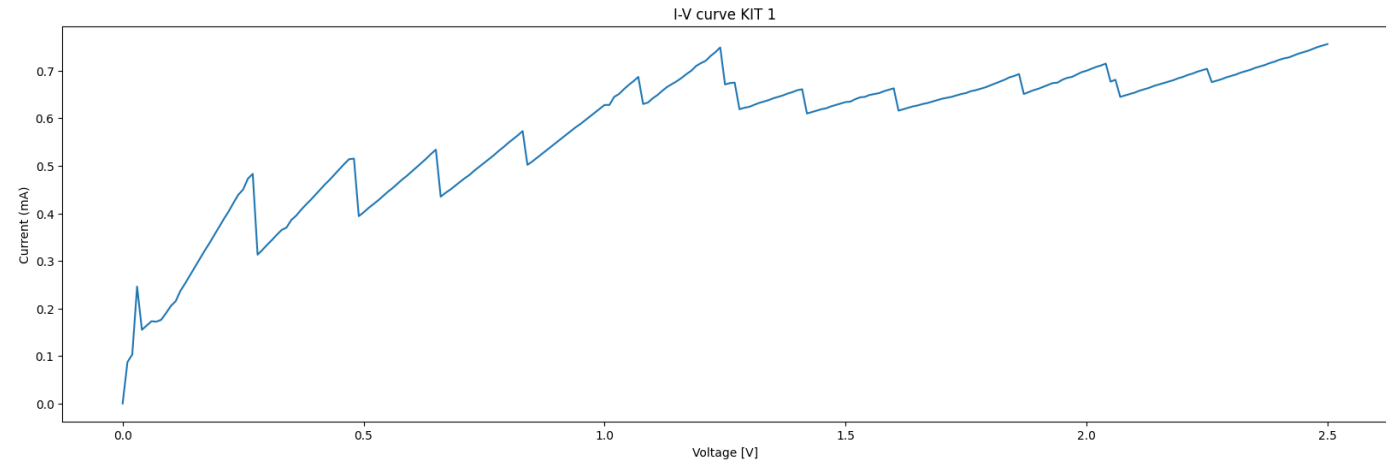




Resistive measurements

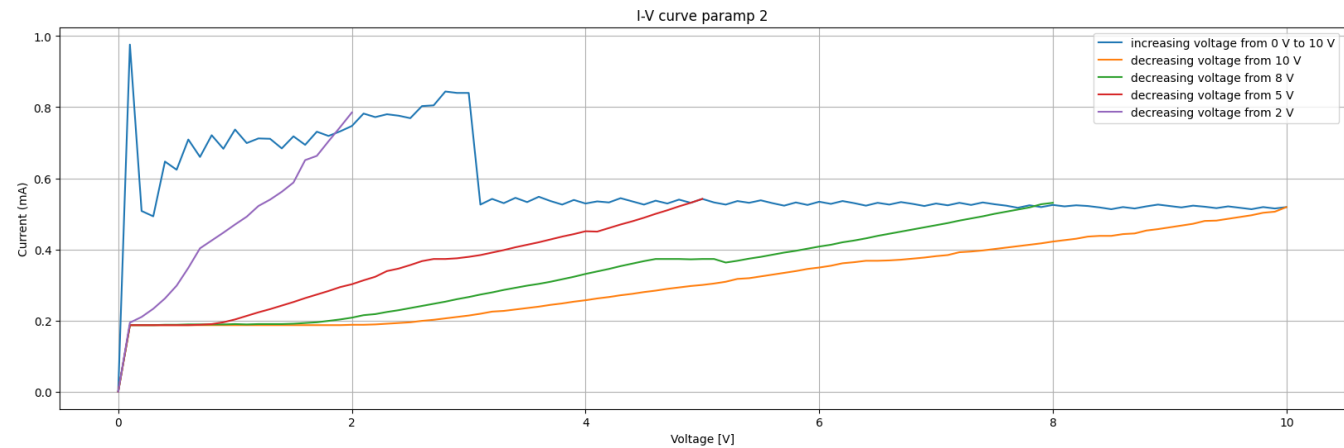
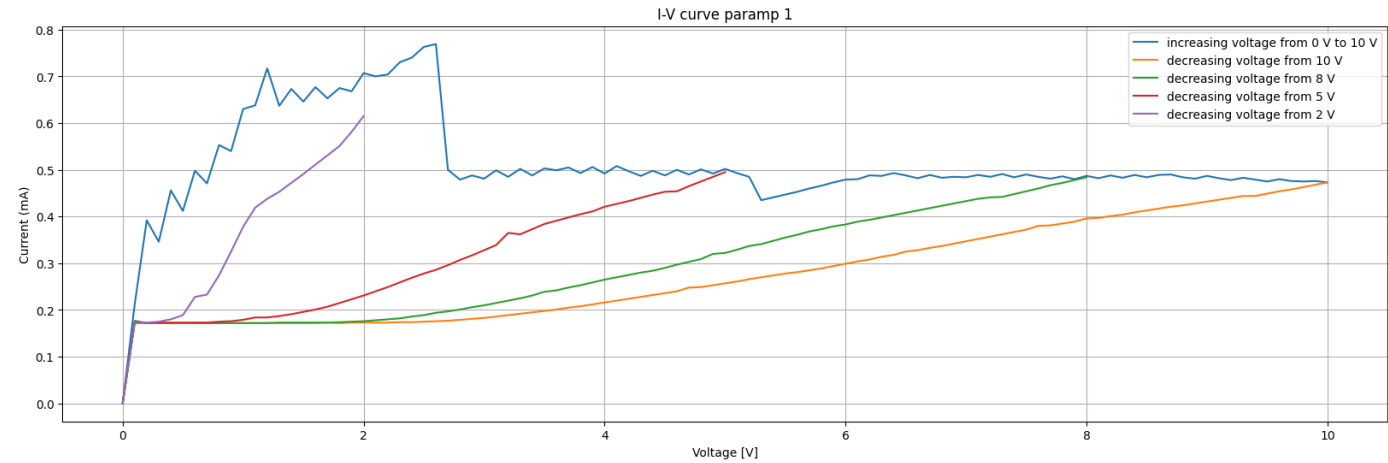
Strange I-V curves

- Measurements w/o any resistance in series
- Between 0 and 3 V
- The current doesn't seem to go above a certain critical value
- A strange jagged I-V curve appears



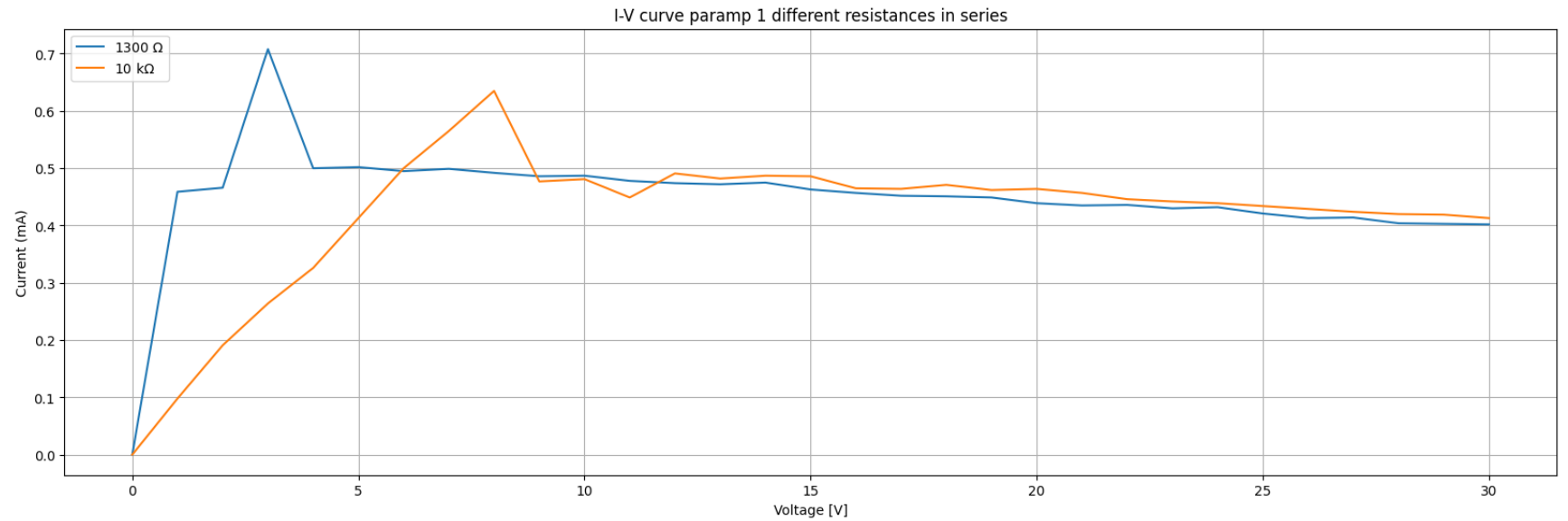
Hysteretic behaviour

- Measurements w/o any resistors in series
- Sweeping upwards from 0 V to 10 V gives a jagged increase, until the current drops and stabilizes.
- Sweeping down from different voltages yields different curves



With resistors in series

- Putting a resistor in series with the bias line reveals that before the critical current the behavior is ohmic!
- The critical current is roughly the same



Likely shorts to ground

- The resistance at the ends of the line looks fine
- The resistance to ground should be in order of $M\Omega$, I'm likely having shorts.

	bias tee on port 1 - bias tee on port 2	bias tee - ground
KIT ₁	0.9 Ω	444 Ω
KIT ₂	1.5 Ω	1.76 k Ω



Experimenting with TDR measurements

The state of the cryostate

- At this point I was sure about having malfunctioning chips:
- The one with 444Ω towards ground was removed, and I measured the S parameters of its line at 4 K for later de-embedding
- The other one was kept in the cryostate, to make some experience with TDR measurements
- I am using an Agilent PNA Series Network Analyzer, that can simulate TDR measurements computing the IFFT of the S parameters, it doesn't perform real Time Domain measurements

TDR of the first section

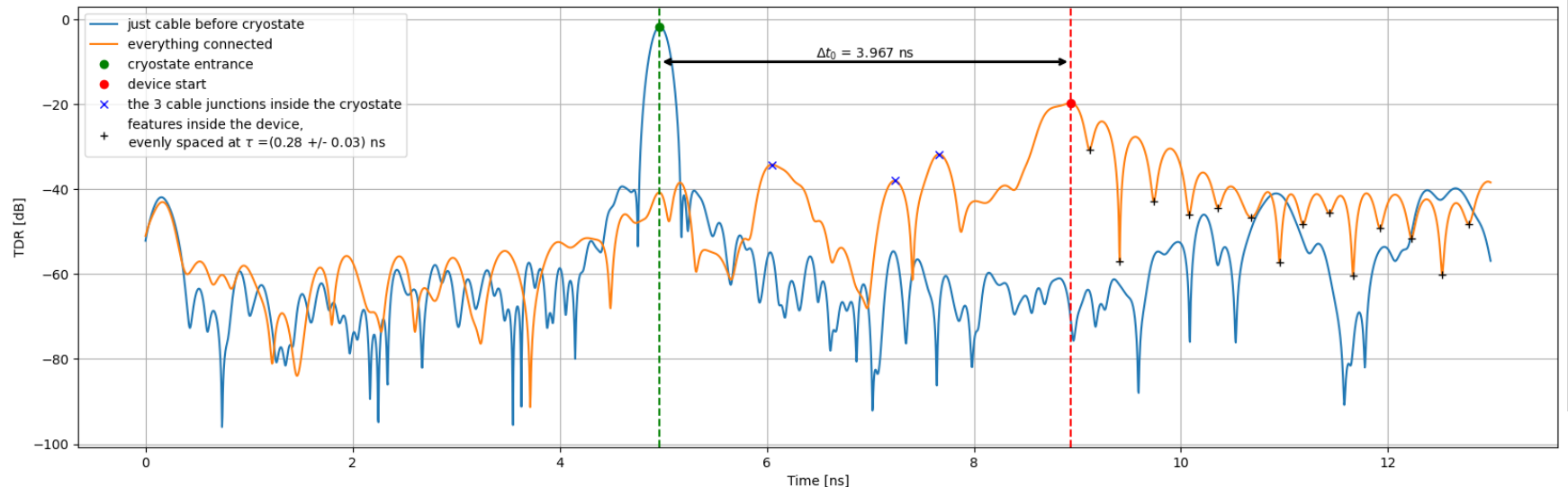
- Phase velocity inferred with stopband position:

$$v_{ph} = f_{stop} \cdot (N_U + N_L) = 7.137 \text{ GHz} \cdot 66 \text{ cells} = 471.042 \text{ cell/ns}$$

- $\tau = 3.967 \text{ ns}$ corresponds to

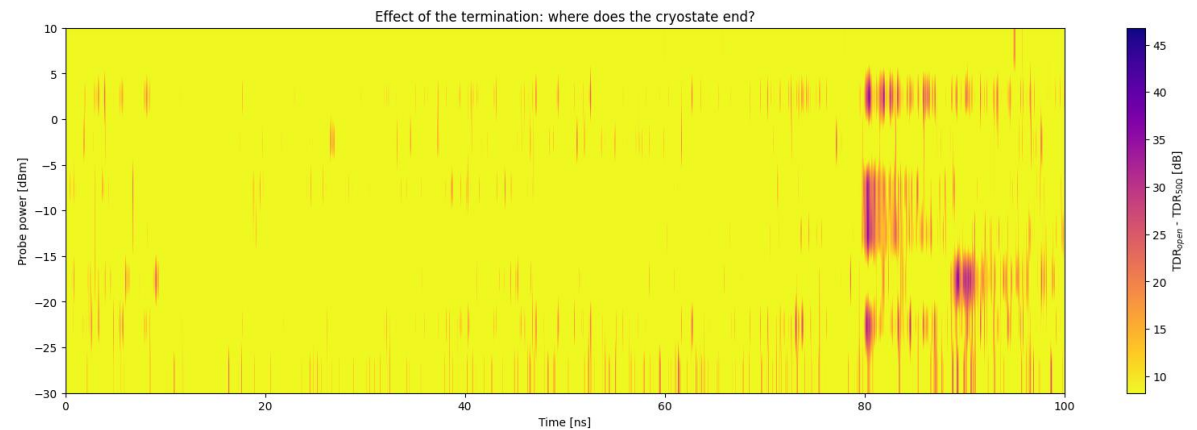
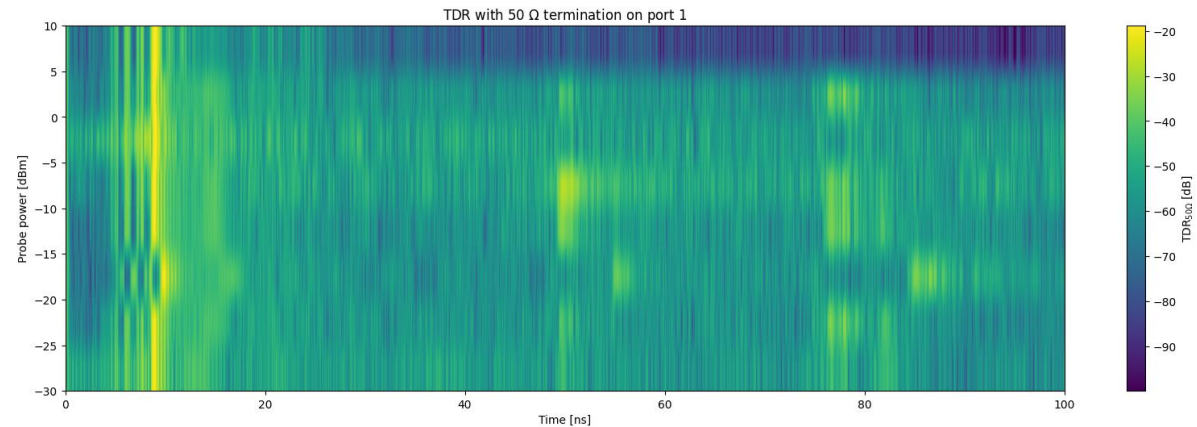
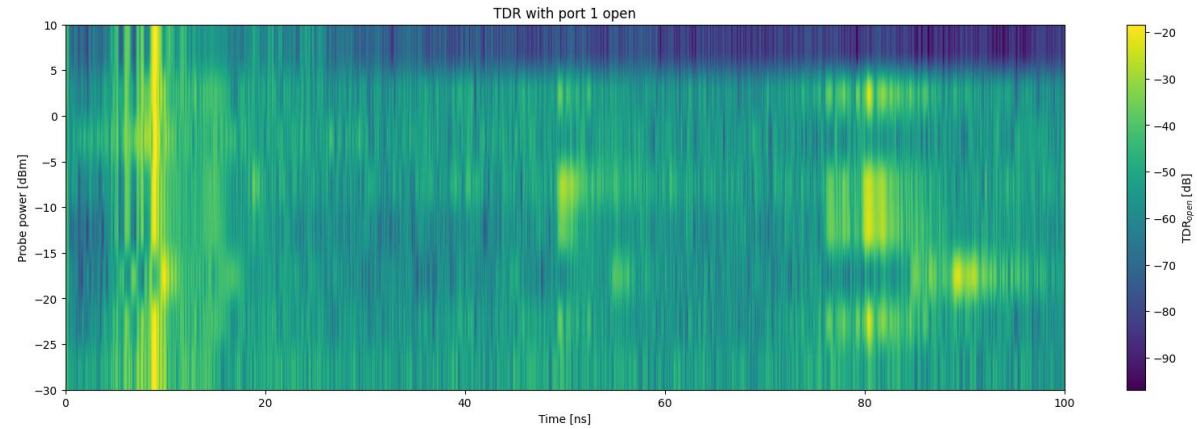
$$\Delta n = 471.042 \text{ cell/ns} \cdot (0.28 \pm 0.03) \text{ ns} = (132 \pm 14) \text{ cells} = 2 \cdot (66 \pm 7) \text{ cells} \approx 2 \cdot (N_U + N_L)$$

- That means that I am seeing the periodic 80Ω loadings!
- The line has 34518 cells in total, this means that we should see the edges of the device separated by $\Delta T = 34518 \text{ cells} / (471.042 \text{ cell/ns}) = 73.280 \text{ ns}$



TDR for different probe powers

- I sweep the probe power and acquire the TDR trace for port 1 with an open and with a 50 Ω termination
- The device start is clearly visible (yellow strip on the left)
- The difference between the two tells me where the cryostat ends
- The device end is obtained subtracting $\Delta t_o = 3.967$ ns



Final results for TDR

- I convert the power level from dBm to mA, knowing that $Z = 1.5 \Omega$
- I plot the traverse times for different probe current amplitudes, as well as the corresponding phase velocities
- The values are in the same order of those estimated with the bandgap position (red)
- The fit with the theoretical law is useless

